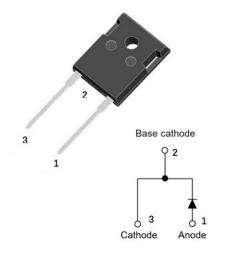


YJD106510NYG4

Silicon Carbide Schottky Diode

V _{RRM}	650V
I _{F (135°C)}	14A
Q _C	31nC



Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

- Package: TO-247AC
- Terminals: Tin plated leads
- Polarity: As marked

■Maximum Ratings (T_c=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE
Device marking code			D106510NYG4
Reverse voltage (Repetitive peak) @ T _j =25°C	V _{RRM}	V	650
Reverse voltage (Surge peak) @ T _j =25°C	V _{RSM}	V	650
Reverse voltage (DC) @ Tj=25°C	V _{DC}	V	650
Continuous forward current @ $T_c=25^{\circ}C$			30
Continuous forward current @ T_c =135°C	I _F	А	14
Continuous forward current @ T_c =151°C			10
Non-repetitive peak forward surge current @ T _c =25°C, tp=10ms, Half Sine Wave	I _{FSM}	А	75
Power Dissipation@ $T_c=25^{\circ}C$	П	w	111
Power Dissipation@ T _C =110°C	P _{TOT}		48
i²t Value@ T _c =25°C ,tp=10ms	∫i²dt	A ² S	28
Operating junction and Storage temperature range	T _j ,T _{stg}	°C	-55 to +175

1/5



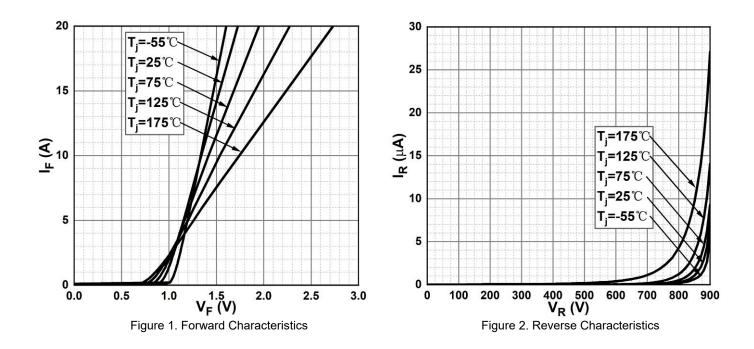
Electrical Characteristics

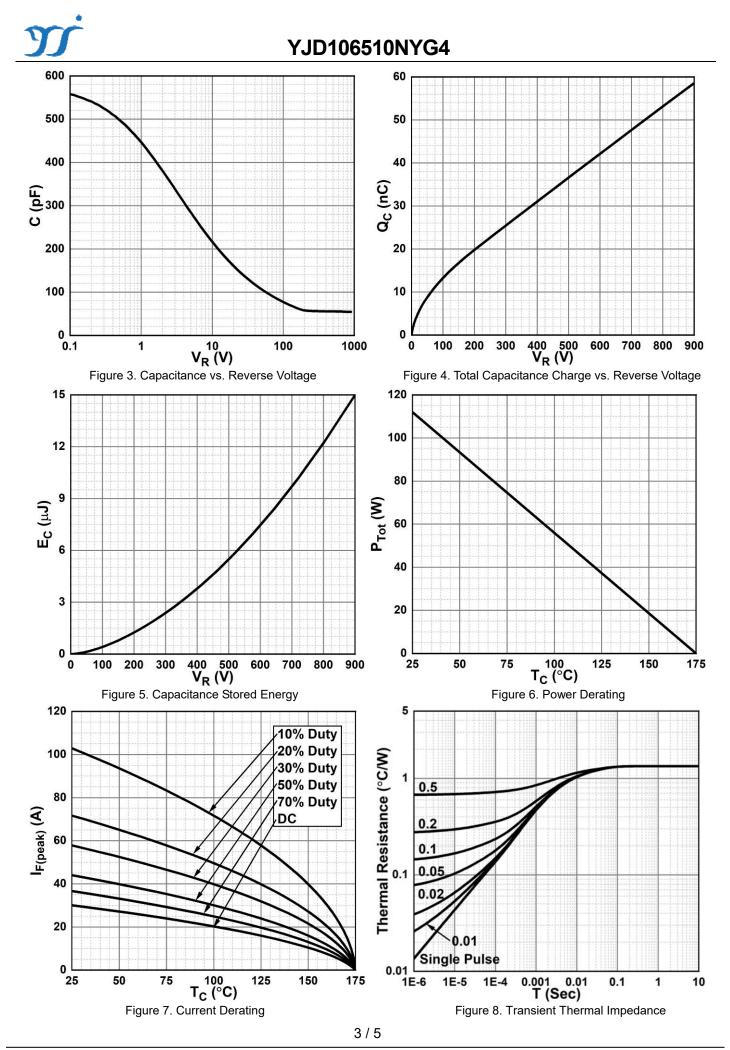
PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	Тур.	Max.
Forward voltage drop	V _F	V	I _F =10A, T _j =25°C	1.35	1.60
			I _F =10A, T _j =175°C	1.75	-
Povoroo ourront			V _R =650V, T _j =25°C	0.2	25
Reverse current	I _R	μA	V _R =650V, T _j =175°C	2	-
Total capacitive charge	Qc	nC	V_R =400V, T _j =25°C , Q_C = $\int_0^{VR} C(V) dV$	31	-
		C pF	V _R =0V, f=1MHZ	568	-
Total capacitance C	С		V _R =200V, f=1MHZ	58	-
			V _R =400V, f=1MHZ	56	-
Capacitance stored energy	Ec	μJ	V _R =400V	3.7	-

■Thermal Characteristics (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE
Thermal resistance	$R_{_{ ext{ hetaJ-C}}}$	°C W	1.34

■Typical Characteristics



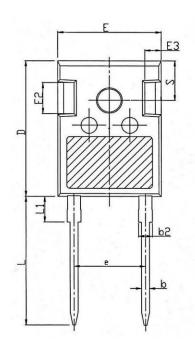


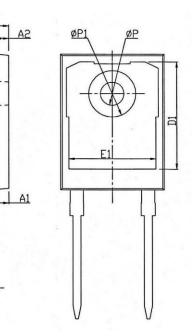
Yangzhou Yangjie Electronic Technology Co., Ltd.



Outline Dimensions

TO-247AC





TO-247AC				
Dim	Min	Max		
А	4.80	5.20		
A1	2.21	2.61		
A2	1.85	2.15		
b	1.11	1.36		
b2	1.91	2.21		
С	0.51	0.75		
D	20.70	21.30		
D1	16.25	16.85		
Е	15.50	16.10		
E1	13.00	13.60		
E2	4.80	5.20		
E3	2.30	2.70		
е	10.88BSC			
L	19.62	20.22		
L1	-	4.30		
ΦP	3.40	3.80		
ΦP1	-	7.30		
S	6.15BSC			

4 / 5



YJD106510NYG4

Disclaimer

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The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of with would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), Yangjie or anyone on its behalf, assumes no responsibility or liability for any damages resulting from such improper use of sale.

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